

HiRel NPN Silicon RF Transistor

- HiRel Discrete and Microwave Semiconductor
- For High Gain Low Noise Amplifiers
- For Oscillators up to 10 GHz
- Noise Figure F = 1.1 dB at 1.8 GHz
 Outstanding Gms = 21dB at 1.8 GHz
- Hermetically sealed microwave package
- Transition Frequency f_T = 22 GHz
- SIEGET[®] 25-Line
 Infineon Technologies Grounded Emitter Transistor-25 GHz f_T-Line



ESA/SCC Detail Spec. No.: 5611/008 Type Variant No. 02

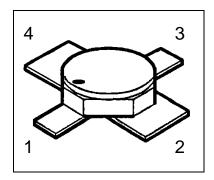
ESD: Electrostatic discharge sensitive device, observe handling precautions!

Туре	Marking	Ordering Code	Pin Configuration		on	Package	
			1	2	3 4		
BFY420 (ql)	-	see below	С	Е	В	Е	Micro-X

(ql) Quality Level: P: Professional Quality

ES: ESA Space Quality

(see order instructions for ordering example)





Maximum Ratings	Corrects of	Values	11:4
Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CEO}	4.5	V
Collector-base voltage	V_{CBO}	15	V
Emitter-base voltage	V_{EBO}	1.5	V
Collector current	I _C	35	mA
Base current	I _B	3.0	mA
Total power dissipation, $T_S \le 129^{\circ}C^{-1), 2)}$	P _{tot}	160	mW
Junction temperature	T _j	175	°C
Operating temperature range	T _{op}	-65+175	°C
Storage temperature range	T _{stg}	-65+175	°C
Thermal Resistance	·	•	
Junction-soldering point 2)	R _{th JS}	< 285	K/W
		•	

- 1) At T_S = + 129 °C. For T_S > + 129 °C derating is required. 2) T_S is measured on the collector lead at the soldering point to the pcb.

Electrical Characteristics

at T_A=25°C; unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-base cutoff current	I _{CBO}	-	-	30	nA
$V_{CB} = 5 \text{ V}, I_E = 0$					
Collector-emitter cutoff current 1.)	I _{CEX}	-	-	200	μΑ
$V_{CE} = 4.5 \text{ V}, I_B = 1.0 \mu A$				(t.b.d.)	
Emitter-base cuttoff current	I _{EBO}	-	-	20	μΑ
$V_{EB} = 1.5 \text{ V}, I_{C} = 0$					
DC current gain	h _{FE}	50	90	150	-
$I_C = 5 \text{ mA}, V_{CE} = 1 \text{ V}$					

Notes:

1.) This Test assures V(BR)CE0 > 4.5V



Electrical Characteristics (continued)

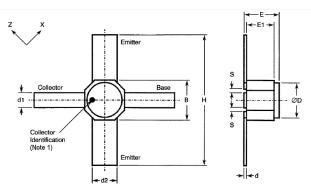
Parameter	Symbol		Values	Unit	
		min.	typ.	max.	
AC Characteristics	·				
Transition frequency	f⊤				GHz
$I_C = 30 \text{mA}, V_{CE} = 3 \text{ V}, f = 2.0 \text{ GHz}$		20	22	-	
Collector-base capacitance	C _{CB}	-	0.14	0.9	pF
$V_{CB} = 2 \text{ V}, V_{BE} = \text{vbe} = 0, f = 1 \text{ MHz}$					
Collector-emitter capacitance	C _{CE}	-	0.46	0.85	pF
$V_{CE} = 2 \text{ V}, V_{BE} = \text{vbe} = 0, f = 1 \text{ MHz}$					
Emitter-base capacitance	C _{EB}	-	0.67	3.0	pF
$V_{EB} = 0.5V$, $V_{CB} = vcb = 0$, $f = 1 MHz$					
Noise Figure	F	-	1.1	1.7	dB
$I_C = 5$ mA, $V_{CE} = 2$ V, $f = 1.8$ GHz,					
$Z_S = Z_{sopt}$					
Insertion power gain	$\left S_{21e}\right ^2$	14	18	-	dB
$I_C = 20 \text{ mA}, V_{CE} = 2 \text{ V}, f = 1.8 \text{ GHz}$					
$Z_S = Z_L = 50 \Omega$					
Power gain	Gms 1.)	-	21	-	dB
$I_C = 20 \text{ mA}, V_{CE} = 2 \text{ V}, f = 1.8 \text{ GHz}$					
$Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$					
1dB Compression point	P _{-1dB}	-	12	-	dBm
I_C = 20 mA, V_{CE} = 2 V, f = 1.8 GHz					
$Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$					

Notes.:

$$1) \quad G_{ms} = \left| \frac{S21}{S12} \right|$$



Micro-X Package



Symbols	Dimensions mm			
	Min	Max		
В	1.68	1.88		
d	0.07	0.15		
d1	0.4	0.6		
d2	0.92	1.12		
ØD	1.55	1.85		
E	0.85	1.25		
E1	0.66	0.86		
Н	4	4.4		
S	0.08	0.3		

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